SUPPLEMENTARY INFORMATION

Fabrication of n$^+$-poly-Si/p$^+$-c-Si tunnel diode using Low-pressure Chemical Vapor Deposition for Photovoltaic Applications

*Vineet Kumar Singh**,

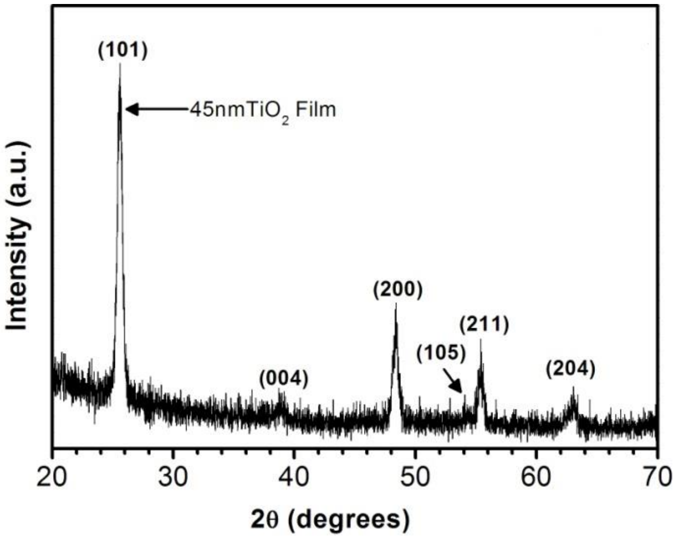

Fig. S1. Grazing incident X-ray diffraction (GIXRD) pattern of TiO_2 film.

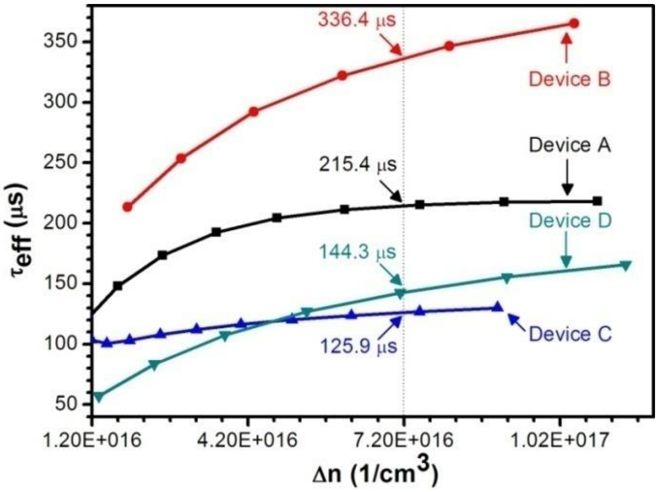

Fig. S2 Effective minority carrier recombination life time dependence on excess electron concentration (Δn) at λ=980 nm and 85 mW laser power.

Department of Physics, DDU Gorakhpur University, Gorakhpur-273009, India
*Corresponding author: E-mail: 1vineetkumarsingh@gmail.com

DOI: 10.5185/amlett.2022.021693